

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1 (Canceled).

2. (Currently amended) A light emitting module comprising:

a light emitting device comprising a pixel section and a sensor section which are formed on a same insulating body; and

a correction circuit connected to the light emitting device,

wherein said correction circuit adjusts luminance of a light emitting element of the pixel section according to environmental illuminance sensed by the sensor section and for keeping a ratio of the luminance to the environmental illuminance at a constant value by the correction circuit,

wherein said sensor section is disposed outside said pixel section[[.]] , and

wherein said sensor section comprises at least one optical sensor comprising a photodiode, a reset TFT, a buffer TFT and a constant current TFT.

3. (Canceled)

4. (Original) A light emitting module according to claim 2, wherein the sensor section includes a thin film photodiode.

5. (Currently amended) A light emitting module comprising:

a light emitting device comprising a pixel section and a sensor section sensing environmental illuminance which are formed on a same insulating body; and

a correction circuit connected to the light emitting device,

wherein the pixel section comprises a thin film light emitting element, and

wherein the sensor section includes a thin film photodiode, and

wherein the sensor section is disposed outside said pixel section[[]], and

wherein said sensor section comprises at least one optical sensor comprising a photodiode, a reset TFT, a buffer TFT and a constant current TFT.

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6. (Currently amended) A light emitting module comprising:

a light emitting device comprising a pixel section, a driving circuit, and a sensor section sensing environmental illuminance which are formed on a same insulating body; and

a correction circuit connected to the light emitting device,

wherein the pixel section includes a thin film light emitting element, and

wherein the sensor section includes a thin film photodiode, and

wherein said sensor section is disposed outside said pixel section[[]] , and

wherein said sensor section comprises at least one optical sensor comprising a photodiode, a reset TFT, a buffer TFT and a constant current TFT.

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7. (Original) A light emitting module according to claim 2, wherein the correction circuit comprises an arithmetic circuit for calculating the luminance of the light emitting element based on a signal transmitted from the sensor section.

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~~12~~
8. (Original) A light emitting module according to claim ~~5~~¹¹, wherein the correction circuit comprises an arithmetic circuit for calculating the luminance of the light emitting element based on a signal transmitted from the sensor section.

~~21~~
9. (Original) A light emitting module according to claim ~~6~~²⁰, wherein the correction circuit comprises an arithmetic circuit for calculating the luminance of the light emitting element based on a signal transmitted from the sensor section.

[10. (Canceled)

~~4~~
11. (Original) A light emitting module according to claim ~~4~~², wherein the light emitting element and the thin film diode are electrically connected to a transistor.

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~~13~~
12. (Original) A light emitting module according to claim ~~5~~¹¹, wherein the light emitting element and the thin film photodiode are electrically connected to a transistor.

~~22~~
13. (Original) A light emitting module according to claim ~~6~~²⁰, wherein the light emitting element and the thin film photodiode are electrically connected to a transistor.

[14. (Canceled)

~~5~~
15. (Original) A light emitting module according to claim ~~11~~⁴, wherein the transistor is a bottom gate type thin film transistor.

¹⁴
~~16~~. (Original) A light emitting module according to claim ~~12~~¹³, wherein the transistor is a bottom gate type thin film transistor.

²³
~~17~~. (Original) A light emitting module according to claim ~~13~~²², wherein the transistor is a bottom gate type thin film transistor.

☐ 18. (Canceled)

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~~19~~. (Original) A light emitting module according to claim ~~2~~¹, wherein the light emitting element is an EL element.

¹⁵
~~20~~. (Original) A light emitting module according to claim ~~5~~¹¹, wherein the light emitting element is an EL element.

²⁴
~~21~~. (Original) A light emitting module according to claim ~~6~~²⁰, wherein the light emitting element is an EL element.

☐ 22. (Canceled)

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~~23~~. (Original) A light emitting module according to claim ~~2~~¹, wherein the light emitting module is included in one of a portable telephone, a video camera, a digital camera, a computer, and a portable telephone.

¹⁶
24. (Original) A light emitting module according to claim ¹¹~~5~~, wherein the light emitting module is included in one of a portable telephone, a video camera, a digital camera, a computer, and portable telephone.

²⁵
25. (Original) A light emitting module according to claim ²⁰~~6~~, wherein the light emitting module is included in one of a portable telephone, a video camera, a digital camera, a computer, and a portable telephone.

[26 – 30 (Canceled).

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31. (Original) A light emitting module according to claim ¹~~2~~, wherein said sensor section comprises at least one optical sensor comprising a photodiode, a first reset TFT, a buffer TFT, a load capacitance, and a second reset TFT.

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32. (Original) A light emitting module according to claim ¹⁴~~5~~, wherein said sensor section comprises at least one optical sensor comprising a photodiode, a first reset TFT, a buffer TFT, a load capacitance, and a second reset TFT.

²⁶
33. (Original) A light emitting module according to claim ²⁰~~6~~, wherein said sensor section comprises at least one optical sensor comprising a photodiode, a first reset TFT, a buffer TFT, a load capacitance, and a second reset TFT.

[34. (Canceled)

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35. (Original) A light emitting module according to claim ~~2~~¹, wherein said sensor section comprises at least one optical sensor comprising a photodiode, a reset TFT, a buffer TFT, and a load resistance or a load capacitance.

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36. (Original) A light emitting module according to claim ~~5~~¹¹, wherein said sensor section comprises at least one optical sensor comprising a photodiode, a reset TFT, a buffer TFT, and a load resistance or a load capacitance.

²⁷
37. (Original) A light emitting module according to claim ~~6~~²⁰, wherein said sensor section comprises at least one optical sensor comprising a photodiode, a reset TFT, a buffer TFT, and a load resistance or a load capacitance.

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[38. (Canceled)

¹⁰
39. (Original) A light emitting module according to claim ~~2~~¹, wherein said sensor section comprises at least one optical sensor comprising a photodiode and a reset TFT.

¹⁹
40. (Original) A light emitting module according to claim ~~3~~¹¹, wherein said sensor section comprises at least one optical sensor comprising a photodiode and a reset TFT.

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41. (Original) A light emitting module according to claim ~~6~~²⁰, wherein said sensor section comprises at least one optical sensor comprising a photodiode and a reset TFT.

[42. (Canceled)

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(Currently amended) A method for driving a light emitting module which comprises a light emitting device comprising a pixel section and a sensor section disposed outside said pixel section which are formed on a same insulating body and a correction circuit connected to the light emitting device, said method comprising the steps of:

adjusting luminance of the light emitting element of the pixel section according to environmental illuminance sensed by the sensor section; and

keeping a ratio of the luminance to the environmental illuminance at a constant value by correction circuit[[]],

wherein said sensor section comprises at least one optical sensor comprising a photodiode, a reset TFT, a buffer TFT and a constant current TFT.

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44.

(Previously presented) An electronic device comprising at least one electro luminescence display device, said display device comprising:

a substrate;

at least one pixel comprising an electro luminescence element over said substrate;

at least one first thin film transistor disposed at said pixel for selecting said pixel;

at least one second thin film transistor disposed at said pixel for supplying an electric current through said electro luminescence element;

a data signal side driver circuit for supplying a data signal to said pixel;

a gate signal side driver circuit electrically connected to a gate electrode of said first thin film transistor, wherein each of said data signal side driver circuit and said gate signal side driver circuit comprises third thin film transistors formed over said substrate; and

a sensor section for sensing a light intensity of an environment formed outside said pixel over said substrate, wherein said sensor comprises a photodiode and at least one fourth thin film transistor;

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a correction circuit for receiving an output signal from said sensor section and correcting luminance of said electro luminescence element in accordance with said output signal.

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45. (Original) An electronic device according to claim ³⁰44, wherein said correction circuit is provided over said substrate.

³²
46. (Original) An electronic device according to claim ³⁰44 wherein said electric device is one of a portable telephone, a video camera, a digital camera, a computer, and portable telephone.

³³
47. (Previously presented) An electronic device comprising:

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- a substrate;
- at least one pixel comprising an electro luminescence element over said substrate;
- at least one first thin film transistor disposed at said pixel for selecting said pixel;
- at least one second thin film transistor disposed at said pixel for supplying an electric current through said electro luminescence element;
- at least one third thin film transistor disposed at least one driver circuit over said substrate;
- at least one fourth thin film transistor disposed at a sensor section over said substrate;
- a first insulating layer over said first thin film transistor, said second thin film transistor, said third thin film transistor and said fourth thin film transistor;
- a second insulating layer over said first insulating layer; and
- a photodiode electrically connected with said fourth thin film transistor through said first insulating layer and said second insulating layer, and disposed at said sensor section over said second insulating layer,

wherein said sensor section senses environmental illuminance.

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48. (Previously presented) An electronic device comprising:

a substrate;

at least one pixel comprising an electro luminescence element over said substrate;

at least one first thin film transistor disposed at said pixel for selecting said pixel;

at least one second thin film transistor disposed at said pixel for supplying an electric current through said electro luminescence element;

at least one third thin film transistor disposed at least one driver circuit over said substrate;

at least one fourth thin film transistor disposed at a sensor section over said substrate;

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a first insulating layer over said first thin film transistor, said second thin film transistor, said third thin film transistor and said fourth thin film transistor;

a photodiode electrically connected with said fourth thin film transistor through said first insulating film, disposed at said sensor section over said first insulating layer; and a second insulating layer over said photodiode,

wherein said sensor section senses environmental illuminance.

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49. (Previously presented) A electronic device according to claim 47 further comprising a correction circuit over said substrate.

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50. (Previously presented) A electronic device according to claim 48 further comprising a correction circuit over said substrate.

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